



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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企业微信二维码



企业QQ二维码

## Product Summary

Part Number	R1 (NOM)	R2 (NOM)	Marking
NK-DDTA144ELP	47kΩ	47kΩ	P2

## Features

- Epitaxial Planar Die Construction
- Ultra-Small Leadless Surface Mount Package
- Ideally Suited for Automated Assembly Processes

## Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0009 grams (Approximate)

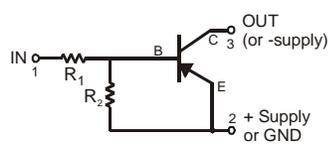
X1-DFN1006-3



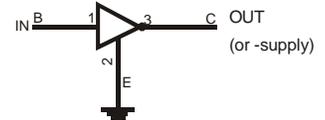
Bottom View



Top View  
Pin-Out



Device Symbol



GND (or +supply)

Equivalent Inverter  
Circuit

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage	V <sub>CC</sub>	-50	V
Input Voltage	V <sub>IN</sub>	+10 to -40	V
Output Current (I <sub>O</sub> )	I <sub>C(MAX)</sub>	-200	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	250	mW
Power Deration above +25°C	P <sub>der</sub>	2	mW/°C
Thermal Resistance, Junction to Ambient Air (Note 5) (Equivalent to one heated junction of PNP)	R <sub>θJA</sub>	500	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>Off Characteristics (Notes 6 &amp; 7)</b>						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-50	—	—	V	I <sub>C</sub> = -10μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-50	—	—	V	I <sub>C</sub> = -1mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-4.5	—	—	V	I <sub>E</sub> = -100μA, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CEX</sub>	—	—	-100	nA	V <sub>CE</sub> = -50V, V <sub>EB(OFF)</sub> = 3V
Base Cutoff Current (I <sub>BEX</sub> )	I <sub>BL</sub>	—	—	-60	μA	V <sub>CE</sub> = -50V, V <sub>EB(OFF)</sub> = 3V
Collector-Base Cut Off Current	I <sub>CBO</sub>	—	—	-100	nA	V <sub>CB</sub> = -50V, I <sub>E</sub> = 0
Collector-Emitter Cut Off Current, I <sub>O(off)</sub>	I <sub>CES</sub>	—	—	-100	nA	V <sub>CE</sub> = -50V, I <sub>B</sub> = 0
Emitter-Base Cut Off Current	I <sub>EBO</sub>	—	—	-100	μA	V <sub>EB</sub> = -4V, I <sub>C</sub> = 0
Input Off Voltage	V <sub>I(off)</sub>	-300	—	—	mV	V <sub>CC</sub> = -5V, I <sub>O</sub> = -100uA
<b>On Characteristics (Notes 6 &amp; 7)</b>						
Input-On Voltage	V <sub>I(on)</sub>	—	—	-3	V	V <sub>O</sub> = -0.3V, I <sub>O</sub> = -5mA
Input Current	I <sub>I</sub>	—	—	-180	μA	V <sub>I</sub> = -5V
DC Current Gain	h <sub>FE</sub>	90	—	—	—	V <sub>CE</sub> = -5V, I <sub>C</sub> = -2.5mA
		120	—	—	—	V <sub>CE</sub> = -5V, I <sub>C</sub> = -5mA
		150	—	—	—	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA
		100	—	—	—	V <sub>CE</sub> = -5V, I <sub>C</sub> = -100mA
		180	—	—	—	V <sub>CE</sub> = -5V, I <sub>C</sub> = -200mA
Output On Voltage (Collector-Emitter Saturation Voltage)	V <sub>O(on)</sub>	—	—	-150	mV	I <sub>I</sub> = -1mA, I <sub>O</sub> = -10mA
		—	—	-800	mV	I <sub>I</sub> = -1mA, I <sub>O</sub> = -40mA
Input Resistance	R <sub>1</sub>	33	47	61	kΩ	—
Resistance Ratio	(R <sub>2</sub> /R <sub>1</sub> )	0.8	1	1.2	—	—
<b>Small Signal Characteristics</b>						
Current Gain-Bandwidth Product	f <sub>T</sub>	—	250	—	MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> = -5mA, f = 100 MHz

- Notes:
5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
  6. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.
  7. Guaranteed by design.

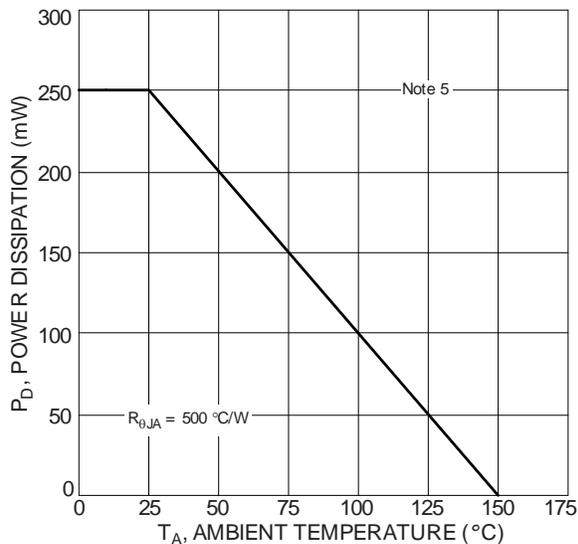


Fig. 1 Power Dissipation vs. Ambient Temperature

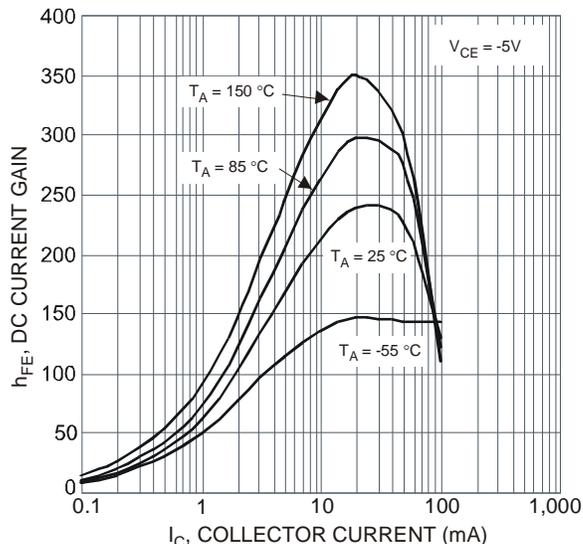


Fig. 2 Typical DC Current Gain vs. Collector Current

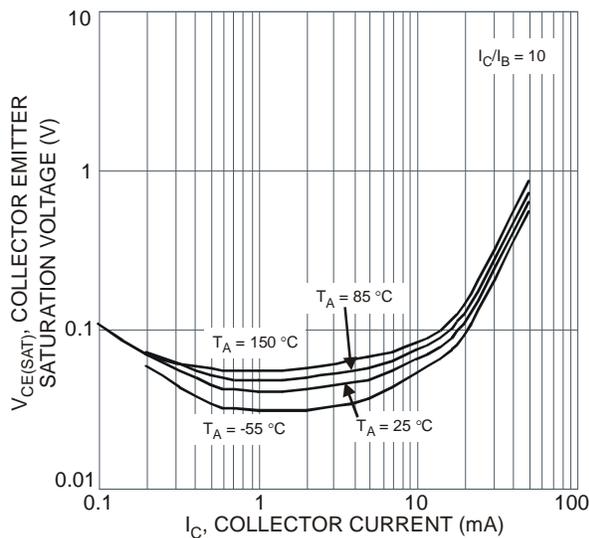


Fig. 3 Typical Collector Emitter Saturation Voltage vs. Collector Current

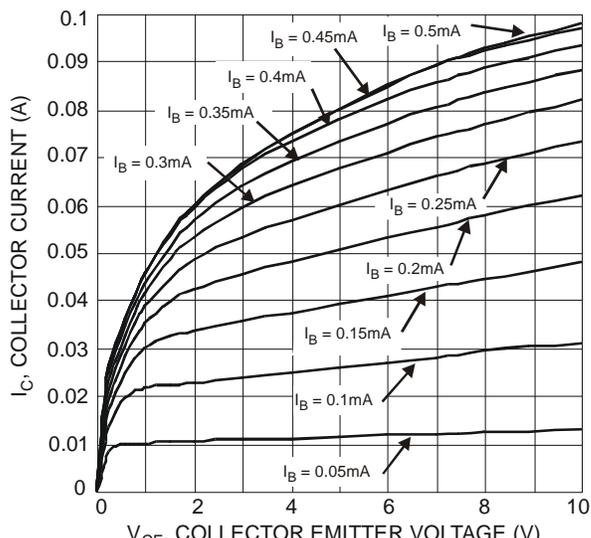


Fig. 4 Typical Collector Emitter Voltage vs. Collector Current

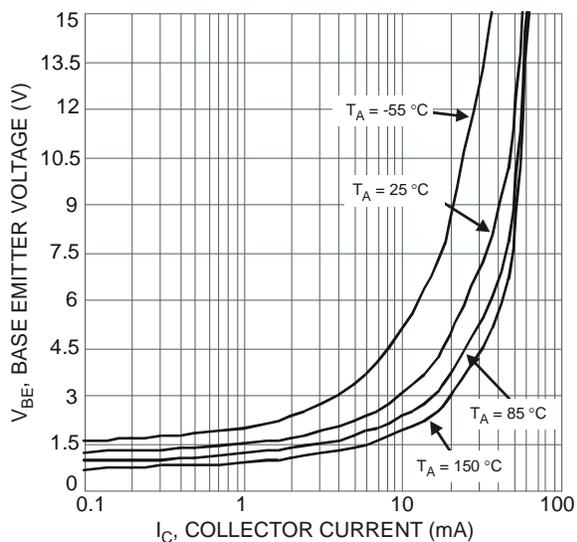


Fig. 5 Typical Base Emitter Voltage vs. Collector Current

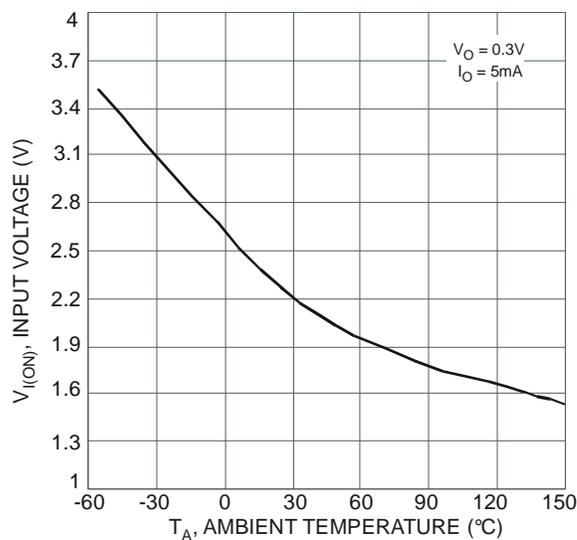


Fig. 6 Typical Input Voltage vs. Ambient Temperature

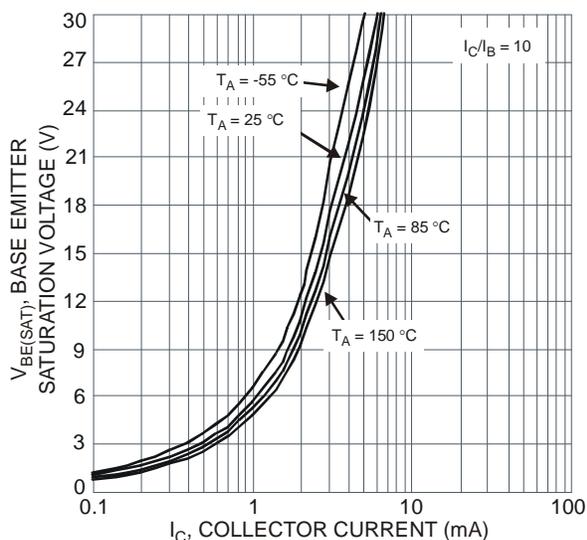
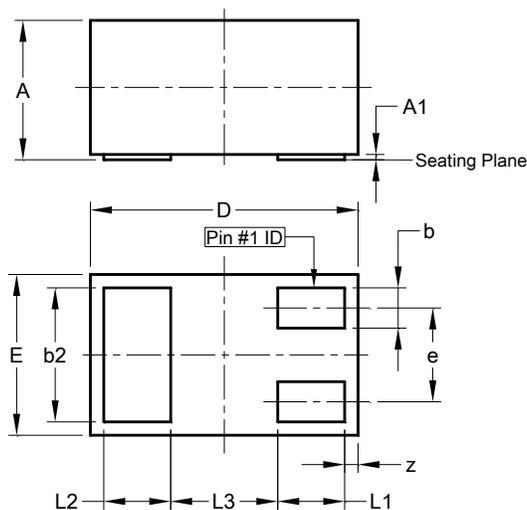


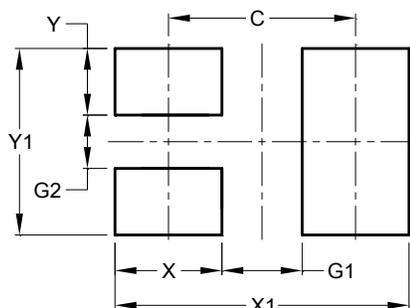
Fig. 7 Typical Base Emitter Saturation Voltage vs. Collector Current

### Package Outline Dimensions



X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

### Suggested Pad Layout



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70